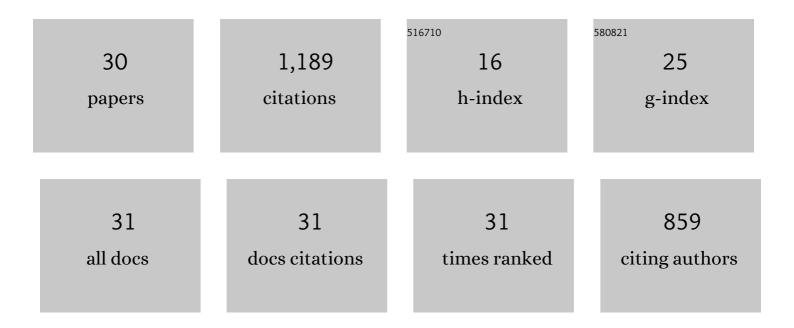


## List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Detection of ultra-low protein concentrations with the simplest possible field effect transistor. Nanotechnology, 2019, 30, 324001.	2.6	12
2	Junctionless nanowire transistor fabricated with high mobility Ge channel. Physica Status Solidi - Rapid Research Letters, 2014, 8, 65-68.	2.4	16
3	Component design and testing for a miniaturised autonomous sensor based on a nanowire materials platform. Microsystem Technologies, 2014, 20, 971-988.	2.0	1
4	Fully CMOS-compatible top-down fabrication of sub-50nm silicon nanowire sensing devices. Microelectronic Engineering, 2014, 118, 47-53.	2.4	14
5	Optimized Laser Thermal Annealing on Germanium for High Dopant Activation and Low Leakage Current. IEEE Transactions on Electron Devices, 2014, 61, 4047-4055.	3.0	39
6	Access resistance reduction in Ge nanowires and substrates based on non-destructive gas-source dopant in-diffusion. Journal of Materials Chemistry C, 2014, 2, 9248-9257.	5.5	18
7	Atomically Flat Low-Resistive Germanide Contacts Formed by Laser Thermal Anneal. IEEE Transactions on Electron Devices, 2013, 60, 2178-2185.	3.0	22
8	Functionalized 3D 7×20-array of vertically stacked SiNW FET for streptavidin sensing. , 2013, , .		2
9	Resist–substrate interface tailoring for generating high-density arrays of Ge and Bi2Se3 nanowires by electron beam lithography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	1.2	17
10	Influence of channel material properties on performance of nanowire transistors. Journal of Applied Physics, 2012, 111, .	2.5	24
11	Bipolar effects in unipolar junctionless transistors. Applied Physics Letters, 2012, 101, 093507.	3.3	39
12	Emission and absorption of optical phonons in Multigate Silicon Nanowire MOSFETs. Journal of Computational Electronics, 2012, 11, 249-265.	2.5	16
13	Intrinsic gate delay and energy-delay product in junctionless nanowire transistors. , 2012, , .		6
14	Electron transport in germanium junctionless nanowire transistors. , 2012, , .		0
15	Device Design and Estimated Performance for p-Type Junctionless Transistors on Bulk Germanium Substrates. IEEE Transactions on Electron Devices, 2012, 59, 2308-2313.	3.0	31
16	Influence of discrete dopant on quantum transport in silicon nanowire transistors. Solid-State Electronics, 2012, 70, 92-100.	1.4	15
17	Improvement of carrier ballisticity in junctionless nanowire transistors. Applied Physics Letters, 2011, 98, .	3.3	43
18	Characterization of a junctionless diode. Applied Physics Letters, 2011, 99, 013502.	3.3	6

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19	Nanowire to Single-Electron Transistor Transition in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 26-32.	3.0	9
20	Influence of Elastic and Inelastic Electron–Phonon Interaction on Quantum Transport in Multigate Silicon Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 1029-1037.	3.0	9
21	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
22	A Simulation Comparison between Junctionless and Inversion-Mode MuGFETs. ECS Transactions, 2011, 35, 63-72.	0.5	29
23	Junctionless Nanowire Transistor: Complementary Metal-Oxide-Semiconductor Without Junctions. Science of Advanced Materials, 2011, 3, 477-482.	0.7	36
24	Effect of intravalley acoustic phonon scattering on quantum transport in multigate silicon nanowire metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 034510.	2.5	19
25	Fabrication of Germanium-on-Insulator by low temperature direct wafer bonding. , 2010, , .		6
26	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
27	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
28	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
29	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17

30 Dissipative transport in Multigate silicon nanowire transistors. , 2010, , .

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